

the plasma confining electrode has a hollow structure, accommodates horizontal gas dispersing plates within the hollow structure for uniformalizing a second gas in the plasma confining electrode, and has holes for introducing the second gas into the substrate processing zone to form a desired film on a deposition substrate located on the deposition substrate area by gas phase chemical reaction of the first gas containing neutral radicals and the second gas with each other; and

the vertical distance between the holes for introducing the second gas into the substrate processing zone and the deposition substrate is no longer than 1,500 times the mean free path λ_g of a blend gas of neutral radicals and the second gas in the substrate processing zone at the time of film formation.--

Amend claim 4 as follows:

--4. (twice amended) A plasma CVD apparatus comprising a substrate processing zone with a deposition substrate area disposed therein, a plasma generating zone for generating plasma of first gas, and a plasma confining electrode for separating the substrate processing zone and the plasma generating zone and confining the first gas and having holes for passing first gas containing neutral radicals from the first gas plasma, wherein

the plasma CVD apparatus further comprises a gas introducing member disposed between the plasma confining electrode member and the deposition substrate and having a plurality of holes, through which a second gas is introduced into